

### **REMARKS**

Entry of this response is proper under 37 CFR §1.116, since no new claims or new issues are presented.

Claims 1-4, 6, 10-15, and 23-30 are all the claims presently pending in the application. Claims 5, 7-9, and 16-22 are canceled.

It is noted that Applicant specifically states that no amendment to any claim herein, if any, should be construed as a disclaimer of any interest in or right to an equivalent of any element or feature of the amended claim.

Claims 1-4, 6, 10-15, and 23-30 stand rejected under 35 U.S.C. § 103(a) as allegedly unpatentable over US Patent 6,909,151 to Hareland, further in view of US Patent Publication 2004/0108559 to Sugii et al.

Claims 1-4, 6, 10-15, and 23-30 stand rejected under 35 U.S.C. § 103(a) as allegedly unpatentable over US Patent 6,909,151 to Hareland, further in view of one or more of previously-cited US Patent Publications: 2004/0227185 to Matsumoto et al., 2004/0075148 to Kumagai et al., and/or 2005/0079677 to Ke et al.

Claims 1-4, 6, 10-15, and 23-30 stand rejected under 35 U.S.C. § 103(a) as allegedly unpatentable over US Patent Publication 2004/0173815 to Yeo et al., further in view of Sugii.

Claims 1-4, 6, 10-15, and 23-30 stand rejected under 35 U.S.C. § 103(a) as allegedly unpatentable over US Patent Publication 2005/0190421 to Chen et al, further in view of Sugii.

Applicants traverse these rejections in the discussion that follows.

#### **I. THE CLAIMED INVENTION**

As described and defined in, for example, claim 1, the present invention is directed to a method of forming a FinFET (Fin Field Effect Transistor) containing a plurality of fins interconnected by fin connectors. At least one localized stressor region is formed within the device, the at least one localized stressor region being located on one of the fin connectors as a region of stressor material filling in an interior portion of the fin connector.

Conventional methods, such as described in paragraphs [0005] through [0007], strain

FinFETs by Si or SiGe, but have caused defects, thereby lowering yields.

The claimed invention, on the other hand, provides a localized stressor embedded within the device.

## **II. THE PRIOR ART REJECTIONS**

In summary, Applicants submit that the prior art rejections of record fail to demonstrate all elements of the claimed invention, since there is no demonstration of providing a localized stressor on the fin connectors of a finFET as a filled-in region on the interior portion of the finFET fin connectors. The closest to this claimed feature would be the application of stressed material on the sides of fins of Sugii. However, this description fails to satisfy the limitation that the localized stressor be applied to the fin connector as a filled-in region of stressor material of the interior of the fin connector.

Hence, turning to the clear language of the claims, in none of the cited references is there a teaching or suggestion of: "... forming at least one localized stressor region within said device, said at least one localized stressor region being located on one of said fin connectors as a region of stressor material filling in an interior portion of said fin connector", as required by independent claim 1. The remaining independent claims have similar language.

Therefore, there are elements of the claimed invention not demonstrated by the rejections of record, and the Examiner is respectfully requested to reconsider and withdraw these rejections.

## **III. FORMAL MATTERS AND CONCLUSION**

In view of the foregoing, Applicant submits that claims 1-4, 6, 10-15, and 23-30, all the claims presently pending in the application, are patentably distinct over the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

Serial No. 10/710,272  
Docket No. FIS920030389US1 (FIS.082)

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Assignee's Deposit Account No. 09-0458.

Respectfully Submitted,



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Frederick E. Cooperrider  
Registration No. 36,769

**McGinn Intellectual Property Law Group, PLLC**  
8321 Old Courthouse Road, Suite 200  
Vienna, VA 22182-3817  
(703) 761-4100  
**Customer No. 21254**

CERTIFICATION OF TRANSMISSION

I certify that I transmitted via EFS this Amendment under 37 CFR §1.116 to Examiner H. Jey Tsai on October 27, 2008.



Frederick E. Cooperrider  
Reg. No. 36,769